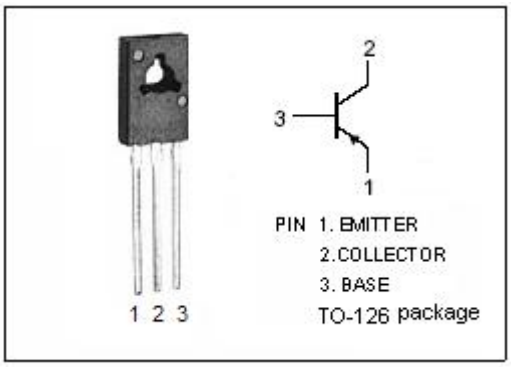
isc Silicon PNP Power Transistor — 2SA1110

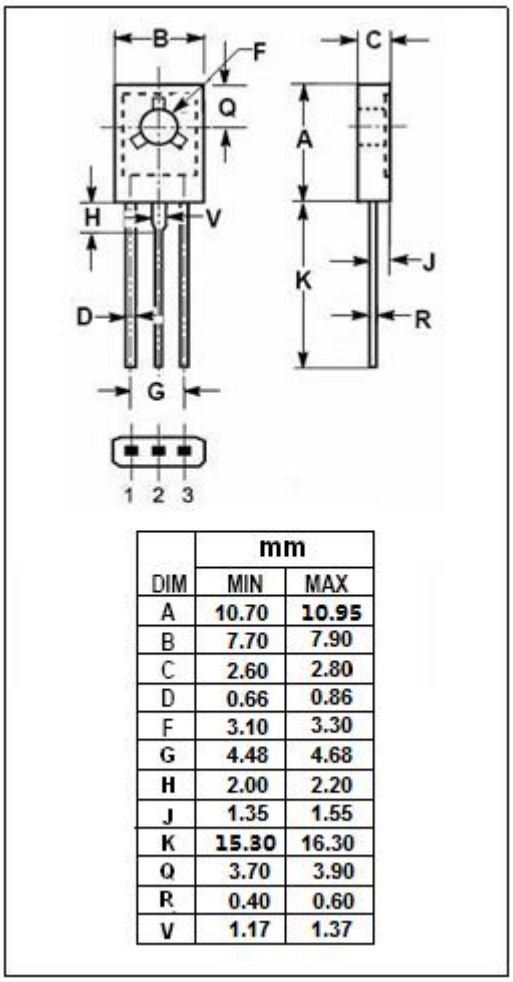
DESCRIPTION

- Collector-Emitter Breakdown Voltage-
  $V_{(BR)CEO}$= -120V (Min)
- Good Linearity of h_{FE}
- Complement to Type 2SC2590
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



APPLICATIONS

- Designed for audio frequency power amplifier applications.



DIM	mm MIN	mm MAX
A	10.70	10.95
B	7.70	7.90
C	2.60	2.80
D	0.66	0.86
F	3.10	3.30
G	4.48	4.68
H	2.00	2.20
J	1.35	1.55
K	15.30	16.30
Q	3.70	3.90
R	0.40	0.60
V	1.17	1.37

ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-120	V
V_{CEO}	Collector-Emitter Voltage	-120	V
V_{EBO}	Emitter-Base Voltage	-5.0	V
I_C	Collector Current-Continuous	-0.5	A
I_{CM}	Collector Current-Peak	-1.0	A
P_C	Collector Power Dissipation	1.2	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= -100 μ A; I_B= 0	-120			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E= -10 μ A; I_C= 0	-5			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -300mA; I_B= -30mA			-1.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= -300mA; I_B= -30mA			-1.2	V
h_{FE-1}	DC Current Gain	I_C= -150mA; V_{CE}= -10V	65		330	
h_{FE-2}	DC Current Gain	I_C= -500mA; V_{CE}= -5V	50			
f_T	Current-Gain—Bandwidth Product	I_E= 50mA; V_{CE}= -10V		200		MHz
C_{OB}	Output Capacitance	I_E= 0; V_{CB}= -10V; f= 1.0MHz		20		pF

◆ **h_{FE-1} Classifications**

P	Q	R	S
65-110	90-155	130-220	185-330